

HEMT Noise Model

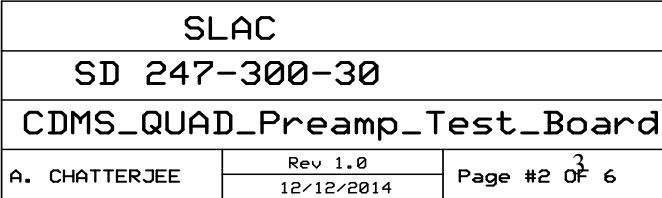
T. Aramaki

Outline

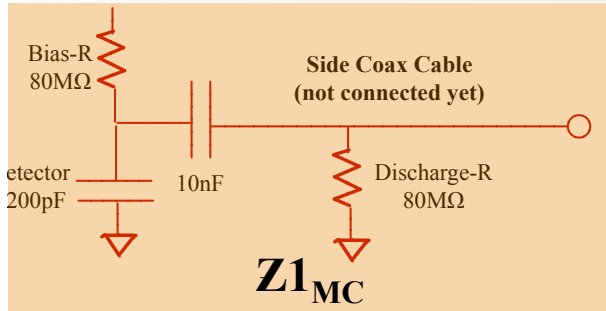
- Noise model was updated based on Gary's note
- New HEMT chips were tested with simplified setup
 - No additional board to avoid unknown stray capacitance etc.
 - $V_{gs} \sim -170\text{mV}$ (was $\sim 0\text{mV}$) for $I_d \sim 0.9\text{mA}$ as expected

Old (VFC#1)

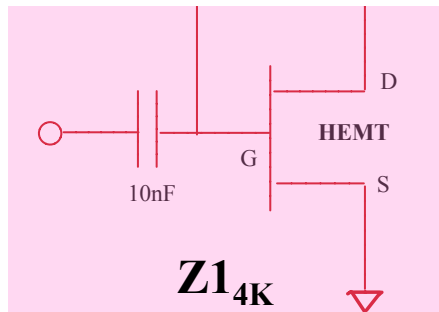
New (VFC#2)



Impedance Calculation

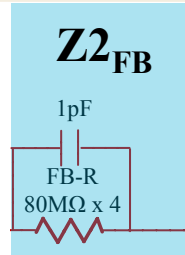


$$Z1_{MC} = \left(\left(\left(i\omega C_{det} + \frac{1}{R_{bias}} \right)^{-1} + \frac{1}{i\omega C_{cc}} \right)^{-1} + \frac{1}{R_{dis}} \right)^{-1}$$

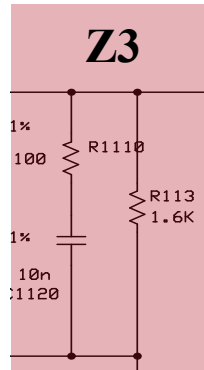


$$Z1_{4K} = \left(\left(R_{open} + \frac{1}{i\omega C_{cc}} \right)^{-1} + i\omega C_{HEMT} \right)^{-1}$$

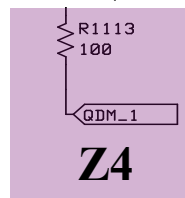
$$Z1_{total} = \left(\frac{1}{Z1_{MC}} + \frac{1}{Z1_{4K}} \right)^{-1} \quad C_{HEMT} = 100\text{pF}$$



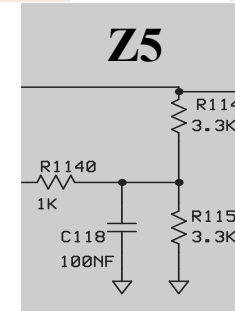
$$Z2_{FB} = \left(i\omega C_{FB} + \frac{1}{R_{FB}} \right)^{-1}$$



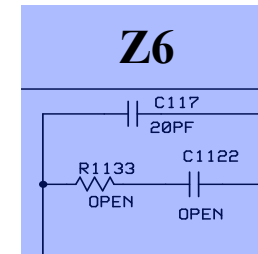
$$Z3 = \left(\frac{1}{R_{113}} + \left(R_{1110} + \frac{1}{i\omega C_{1120}} \right)^{-1} \right)^{-1}$$



$$Z4 = R_{1113}$$



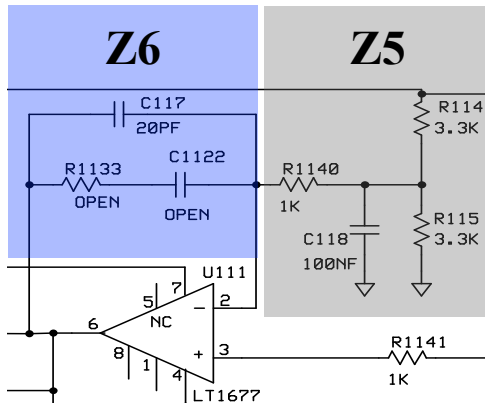
$$Z5 = R_{1140} + \left(i\omega C_{118} + \frac{1}{R_{115}} + \frac{1}{R_{114}} \right)^{-1}$$



$$Z6 = \left(i\omega C_{117} + \frac{1}{R_{open}} \right)^{-1} \quad R_{open} \sim 10^{15}\Omega$$

Gain Calculation

Op-Amp gain



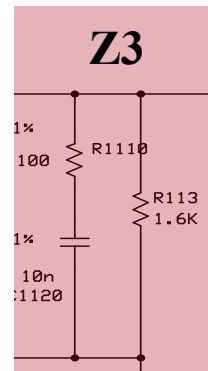
$$A = \frac{A_{open}}{1 + A_{open} B_1}$$

$$A_{open} = \frac{2 \cdot 10^7}{\left(1 + i \frac{\omega}{\omega_1}\right) \left(1 + i \frac{\omega}{\omega_2}\right)}$$

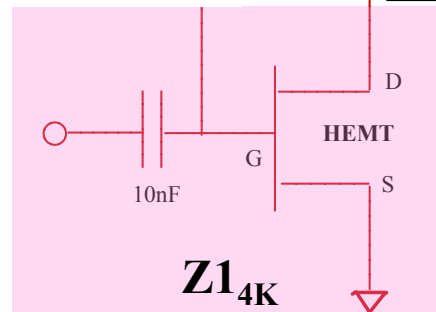
$$f_1 = 0.2\text{Hz}, f_2 = 10\text{kHz}$$

$$B_1 = \frac{Z5}{Z5 + Z6}$$

HEMT gain



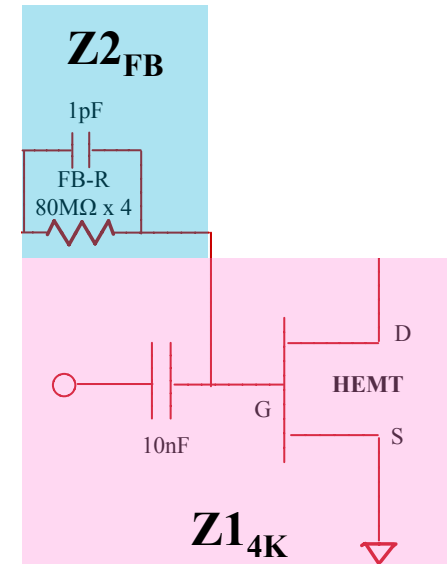
$$g_d = 0.75\text{mS}$$



$$A_{HEMT} = g_m Z3$$

$$g_m = 35\text{mS}$$

Total gain



$$gain = - \frac{A_{total} (1 - B_2)}{1 + A_{total} B_2}$$

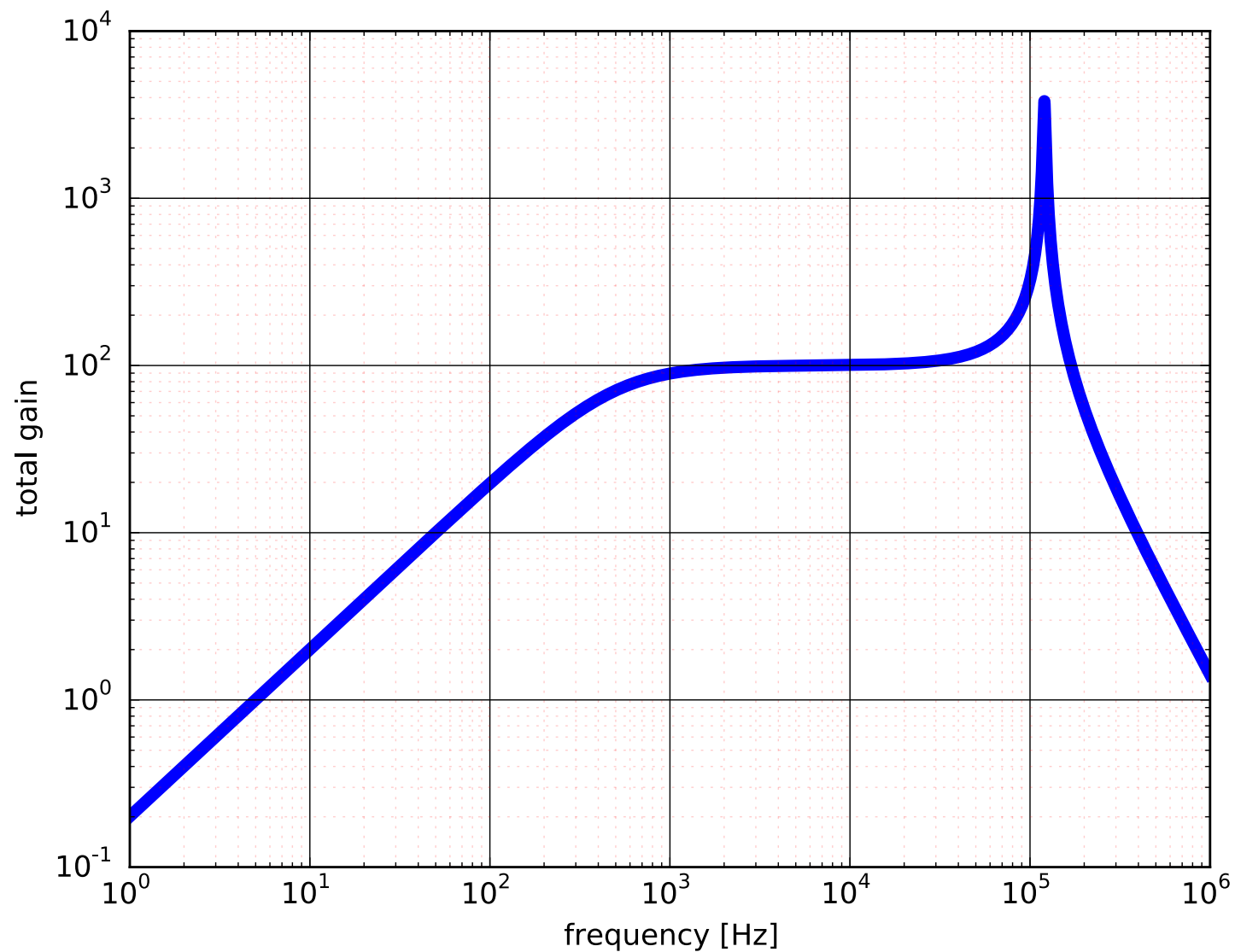
$$B_2 = \frac{Z1}{Z1 + Z2}$$

$$A_{total} = A_{HEMT} A$$

Gain vs. Frequency

No detector, discharge-R, bias-R, $T_{4K} = 5.5K$

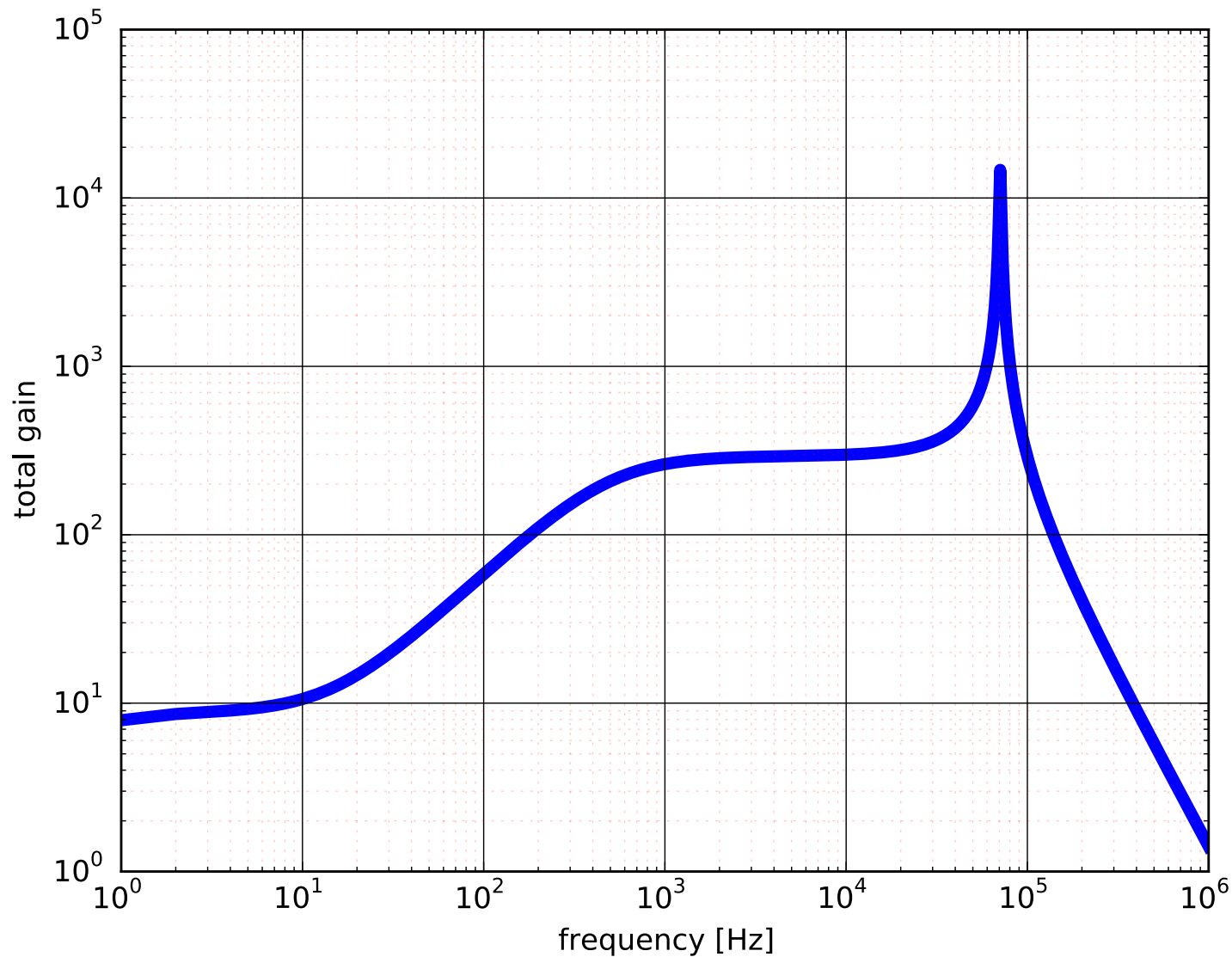
SLAC



Gain vs. Frequency

$C_{\text{det}} = 200\text{pF}$ $R_{\text{dis}} = 80\text{M}\Omega$, $R_{\text{bias}} = 80\text{M}\Omega$, $T_{4\text{K}} = 4\text{K}$, $T_{\text{MC}} = 30\text{mK}$

SLAC



Noise Calculation (at HEMT input)

Thermal Johnson Noise at Z1

$$v_1 = \sqrt{4kT_{MC} \operatorname{Re}(Z1_{MC}) + 4kT_{4K} \operatorname{Re}(Z1_{4K})}$$

Thermal Johnson Noise at Z2_FB

$$v_2 = \frac{\sqrt{4kT_{MC} \operatorname{Re}(Z2_{FB})}}{|gain|}$$

Thermal Johnson Noise at Z3

$$v_3 = \frac{\sqrt{4kT_{MC} \operatorname{Re}(Z3)}}{|A_{HEMT}|}$$

Thermal Johnson Noise at Z4

$$v_4 = \frac{g_d}{g_m} \sqrt{4kT_{MC} \operatorname{Re}(Z4)}$$

Op-amp (LT1677) noise

$$v_{amp} = \sqrt{\left(1.8 \cdot 10^{-9}\right)^2 + \left(30 \cdot 10^{-9}\right)^2 \frac{2\pi}{\omega}}$$

Shot noise at BJT

$$v_{shot} = \frac{\sqrt{2 \cdot 2qI_d}}{g_m}$$

HEMT noise

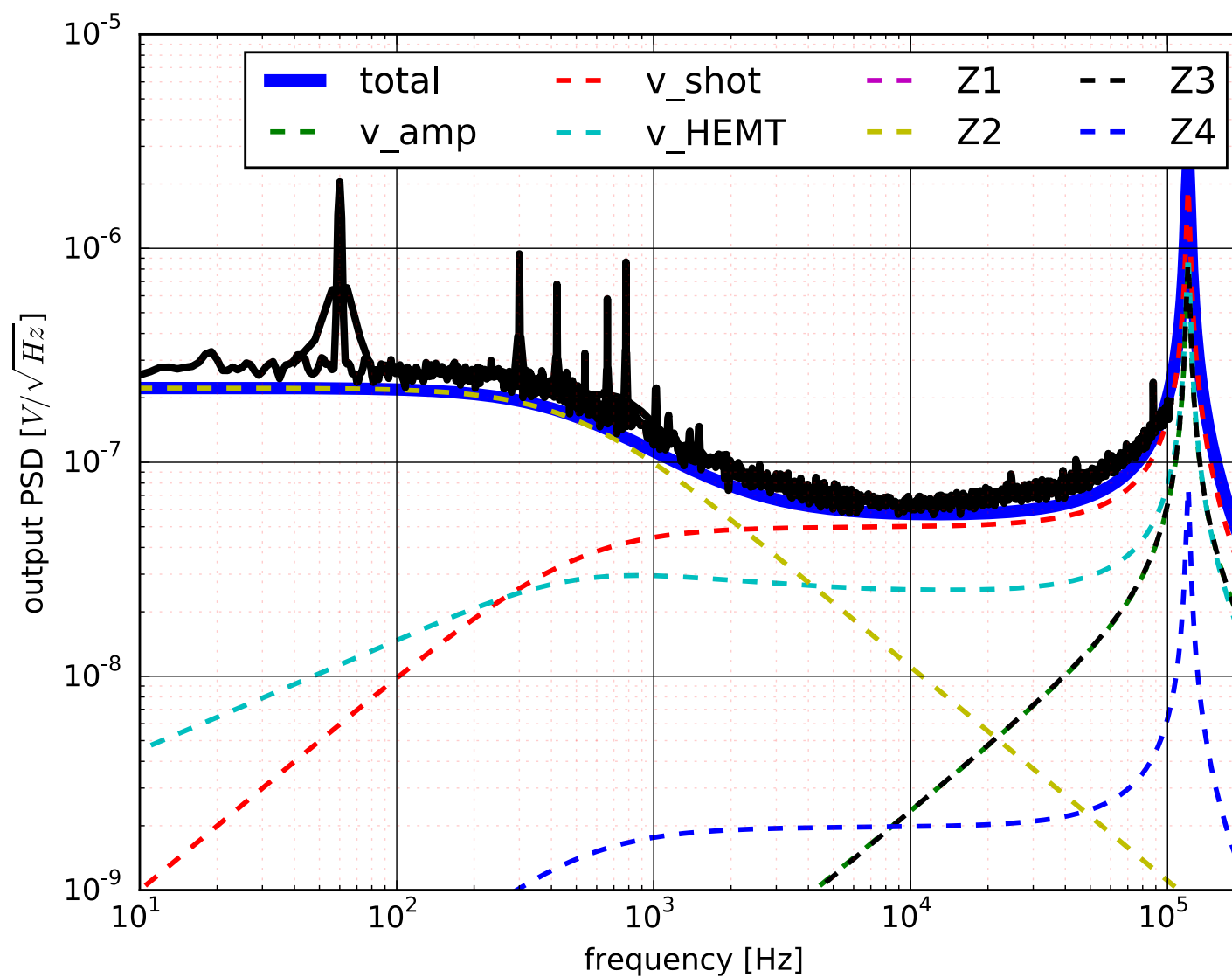
(fit to Yon Jin's plot by Gary)

$$v_{HEMT} = 0.24 \cdot 10^{-9} \sqrt{2 \left(1 + 850 \frac{2\pi}{\omega}\right)}$$

HEMT Output Noise

No detector, discharge-R, bias-R, $T_{4K} = 5.5K$

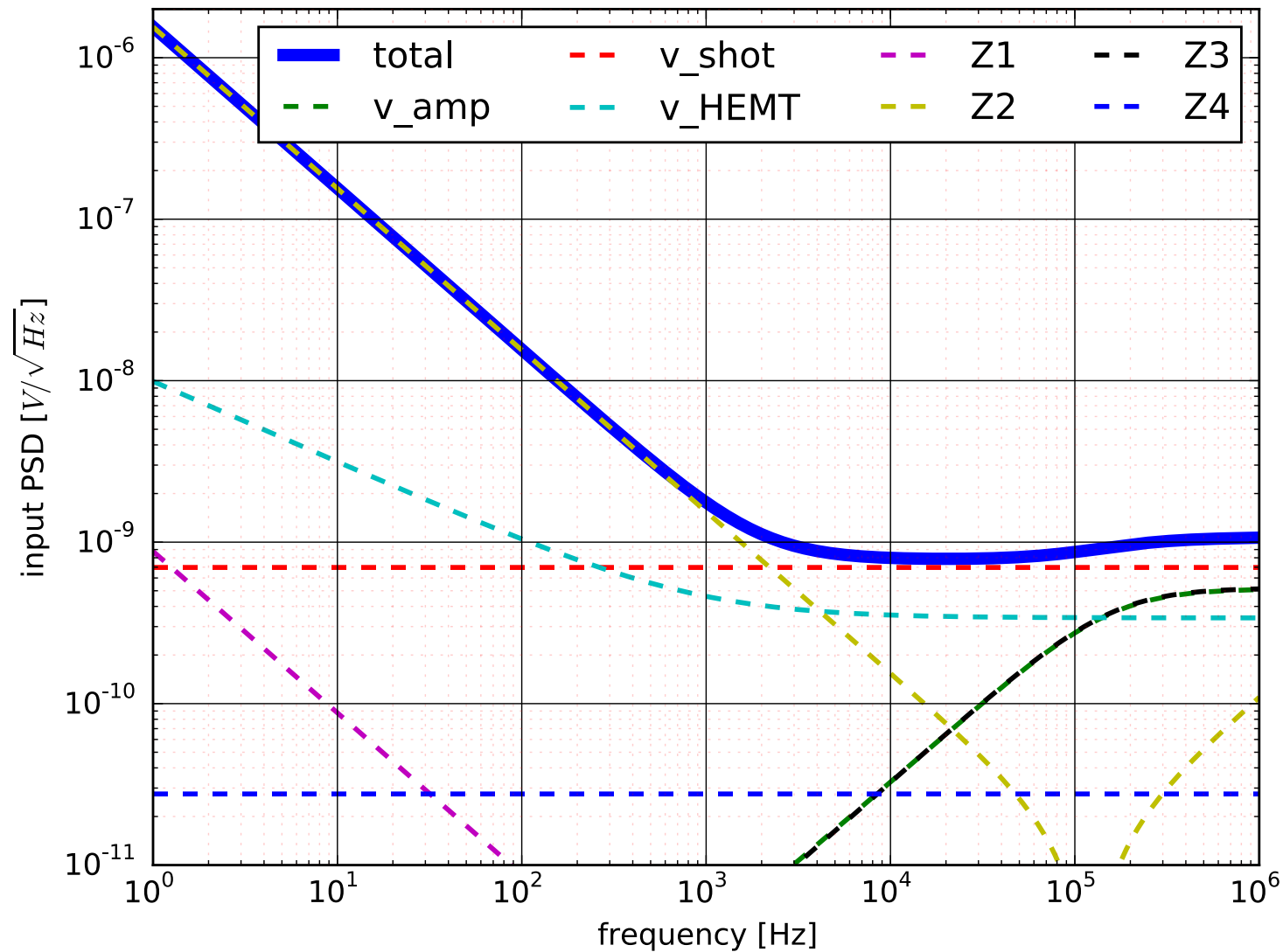
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HEMT Input Noise

No detector, discharge-R, bias-R, $T_{4K} = 5.5K$

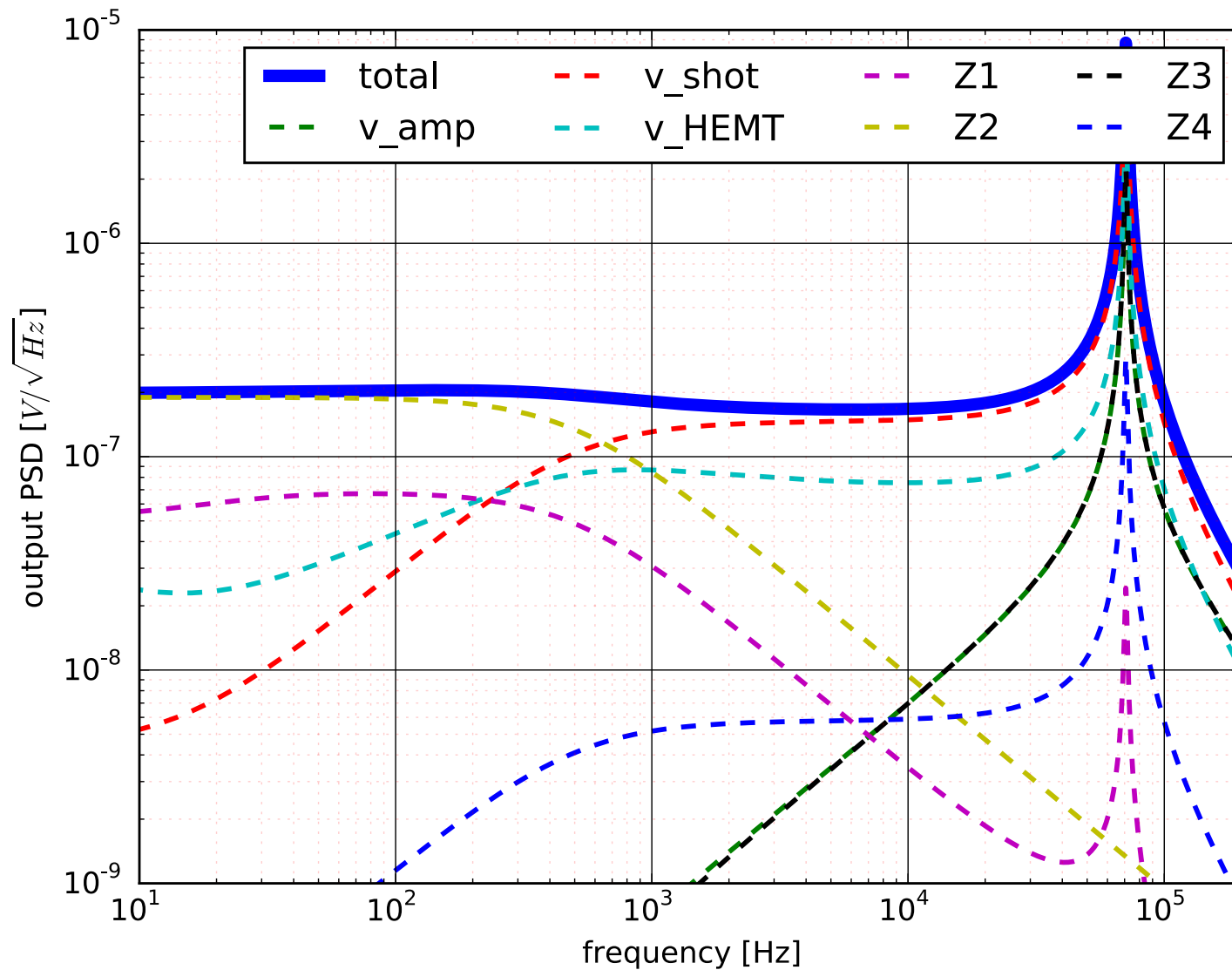
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HEMT Output Noise

$C_{\text{det}} = 200\text{pF}$ $R_{\text{dis}} = 80\text{M}\Omega$, $R_{\text{bias}} = 80\text{M}\Omega$, $T_{4\text{K}} = 4\text{K}$, $T_{\text{MC}} = 30\text{mK}$

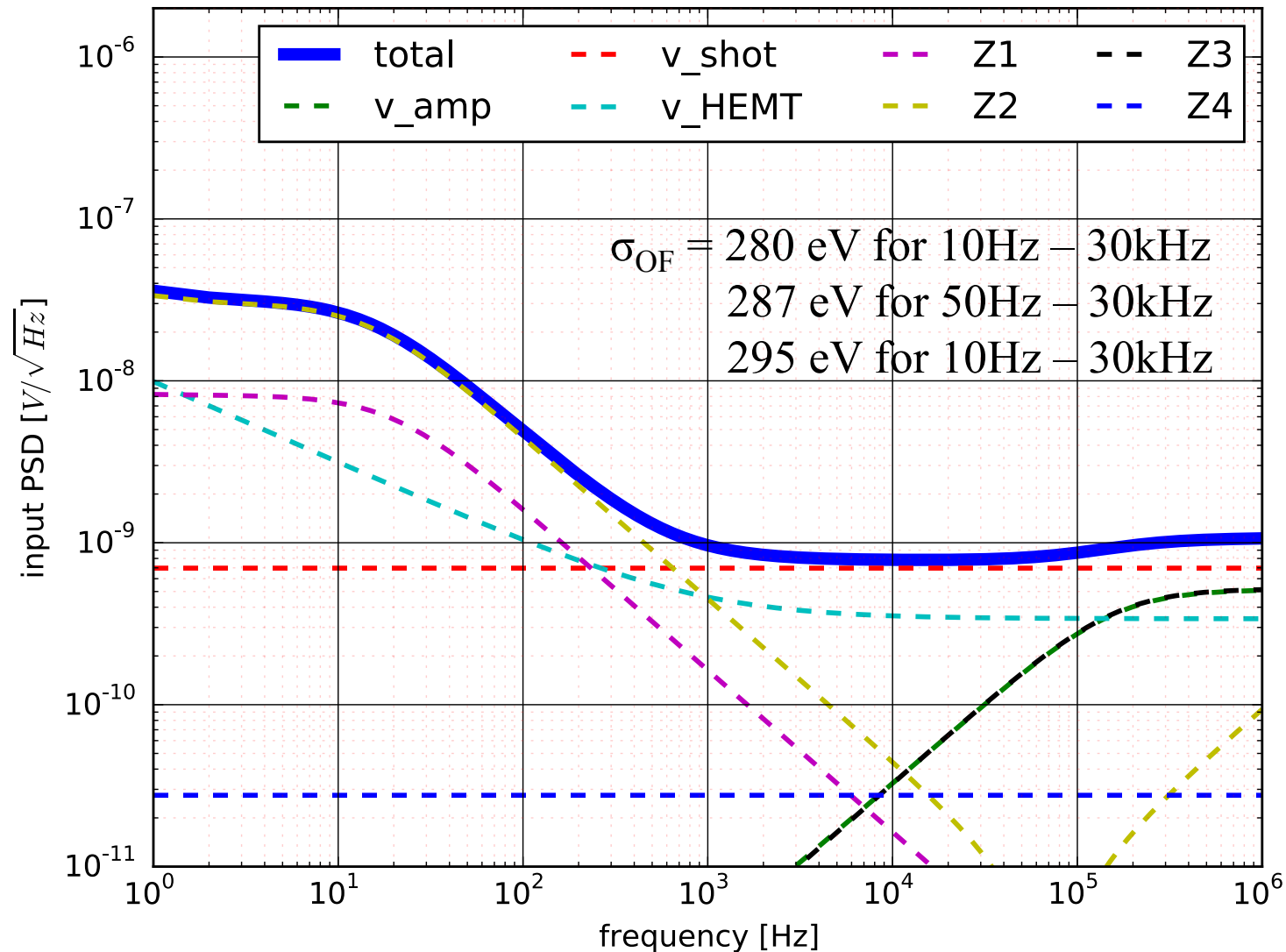
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HEMT Input Noise

$C_{\text{det}} = 200\text{pF}$ $R_{\text{dis}} = 80\text{M}\Omega$, $R_{\text{bias}} = 80\text{M}\Omega$, $T_{4\text{K}} = 4\text{K}$, $T_{\text{MC}} = 30\text{mK}$

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Summary

- With a HEMT chip (and no additional board), we obtained a consistent HEMT noise result with the calculated model.
- Future plan
 - Add more components (C_{det} , R_{dis} , R_{bias}) and compare the noise with the model
 - Measure noise with Vacuum Coax Cable
 - Vibration susceptibility test
 - Vacuum Coax Cable vs. Twisted Pair of Wires
 - Active reset test